



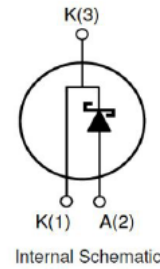
ESIC10120S



Silicon carbide power schottky diode



TO-220AC



Features
• Rated to 1200V at 10 Amps • Zero reverse recovery current • Zero forward recovery voltage • Temperature independent switching behaviour • High temperature operation • High frequency operation • Marking : ESIC10120S

Benefits
• Unipolar rectifier • Substantially reduced switching losses • No thermal run-away with parallel devices • Reduced heat sink requirements

Ordering Information		
Part No.	Package	Packing
ESIC10120S	TO-220AC	50 / Tube

Application
• SMPS, e.g., CCM PFC • Motor drives, Solar application, UPS, Wind turbine, Rail traction, EV/HEV

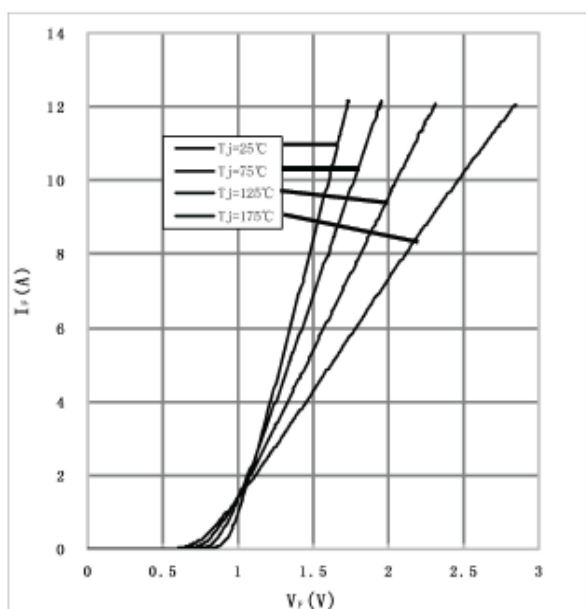
Absolute Maximum Ratings (T _A =25°C unless otherwise specified)				
Parameter	Symbol	Conditions	Limit	Unit
Repetitive Peak Reverse Voltage	V _{RRM}	T _j =25°C	1200	V
Surge Peak Reverse Voltage	V _{RSM}	T _j =25°C	1200	V
DC Blocking Voltage	V _{DC}	T _j =25°C	1200	V
Continuous Forward Current	I _F	T _j =25°C T _j =135°C T _j =150°C	25.9 12.5 10	A
Repetitive Peak Forward Surge Current	I _{FRM}	T _C =25 °C , tp=10ms, Half Sine Wave, D=0.3	50	A
Non-Repetitive Peak Forward Surge Current	I _{FSM}	T _C =25 °C , tp=10ms, Half Sine Wave	60	A
Power Dissipation	P _{TOT}	T _C =25°C	141.5	W
		T _C =110°C	62	W
Maximum Case Temperature	T _C		135	°C
Operating Junction and Storage Temperature	T _j 、 T _{stg}		-55~+175	°C
Mounting Torque		M3 Screw	1	Nm
		6-32 Screw	8.8	lbf-in
Thermal resistance from junction to case	R _{θJC}		1.06 Typ.	°C/W



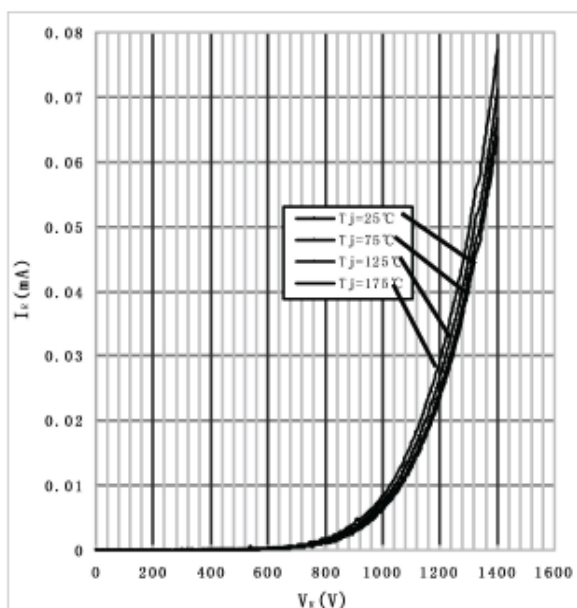
Electrical Characteristics (T _A = 25 °C unless otherwise specified)						
Parameter	Conditions	Symbol	Min.	Typ.	Max.	Unit
Forward Voltage	I _F =10A, T _J =25°C	V _F	-	1.63	1.8	V
	I _F =10A, T _J =175°C		-	2.55	3	
Reverse Current	V _R =1200V, T _J =25°C	I _R	-	50	100	μA
	V _R =1200V, T _J =175°C		-	100	200	
Total Capacitive Charge	V _R =800V, T _J =150°C $Q_C = \int_0^{V_R} C(V) dV$	Q _C	-	69	-	nC
Total Capacitive Charge	V _R =0V, T _J =25°C, f=1MHZ	C	-	770	790	pF
	V _R =400V, T _J =25°C, f=1MHZ		-	52	54	
	V _R =800V, T _J =25°C, f=1MHZ		-	50	51	

Rating and Characteristics Curves

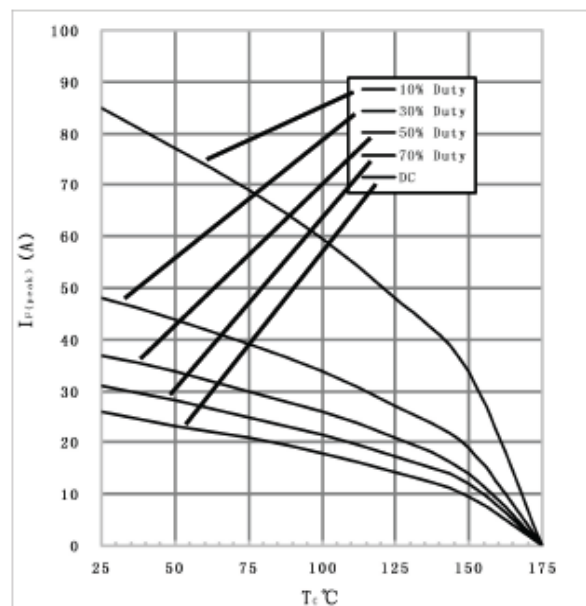
1) Forward IV characteristics as a function of T_J :



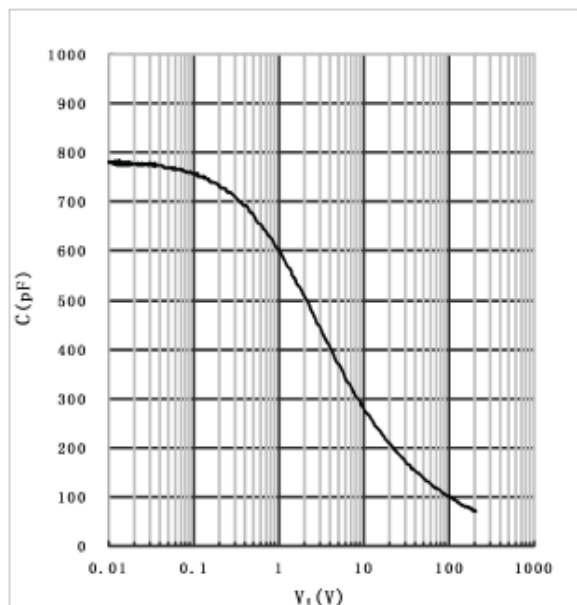
2) Reverse IV characteristics as a function of T_J :



3) Current Derating



4) Capacitance vs. reverse voltage :



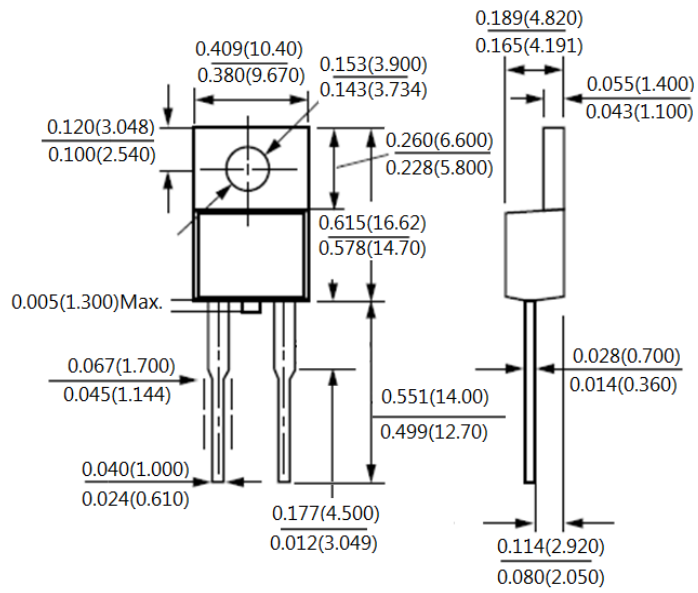


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Package Outline Dimensions



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Dimensions in inches and (millimeters)